

Small Signal Diode

MMBD4148SE, MMBD4148CC, MMBD4148CA

Features

• These are Pb-Free Devices

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Non-Repetitive Peak Forward Surge Current Pulse Width = 1.0 s Pulse Width = 1.0 μs	I _{FSM}	1.0 2.0	A
Operating Junction Temperature Range	TJ	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	350	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

					•
Characteristic	Symbol	Min	Тур	Max	Unit
Breakdown Voltage $I_R = 5.0 \mu A$ $I_R = 100 \mu A$	V _R	75 100	- 1	-	V
Forward Voltage I _F = 10 mA	V _F	I	I	1.0	V
Reverse Leakage Current $V_R = 20 \text{ V}$ $V_R = 20 \text{ V}$, $V_A = 150 ^{\circ}\text{C}$ $V_R = 75 \text{ V}$	I _R			25 50 5.0	nA μA μA
Total Capacitance V _R = 0 V, f = 1.0 MHz	C _T	-	-	4.0	pF
Reverse Recovery Time I_F = 10 mA, V_R = 6.0 V, I_{RR} = 1.0 mA, R_L = 100 Ω	t _{rr}	-	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



MARKING DIAGRAM



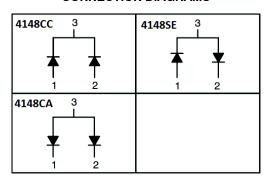
Dx = Device Codex = 4, 5, 6

M = Assembly Operation Month

■ = Pb-Free Package

(Note: Microdot may be in either location)

CONNECTION DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

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TYPICAL PERFORMANCE CHARACTERISTICS

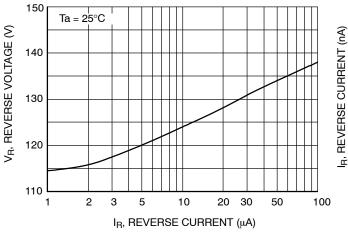


Figure 1. Reverse Voltage vs. Reverse Current BV - 1.0 to 100 μA

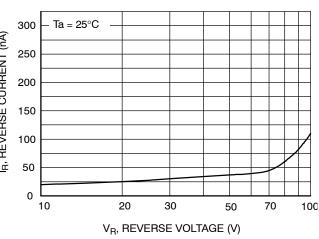


Figure 2. Reverse Current vs. Reverse Voltage IR – 10 to 100 V

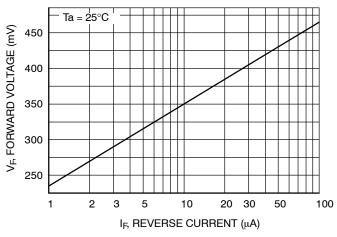


Figure 3. Forward Voltage vs. Forward Current VF - 1.0 to 100 μ A

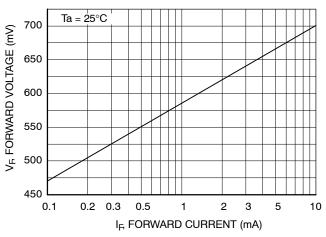


Figure 4. Forward Voltage vs. Forward Current VF – 0.1 to 10 mA

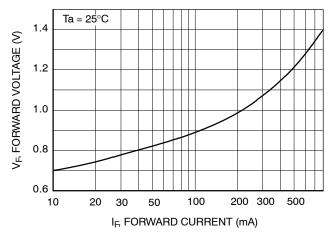


Figure 5. Forward Voltage vs. Forward Current VF – 10 to 800 mA

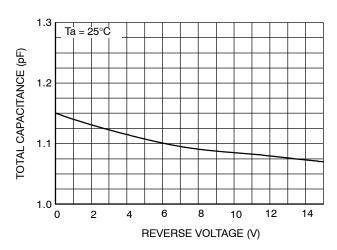


Figure 6. Total Capacitance vs. Reverse Voltage

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TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

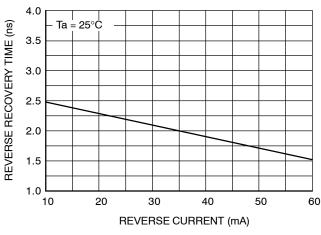


Figure 7. Reverse Recovery Time vs. Reverse Current TRR – IR 10 mA to 60 mA

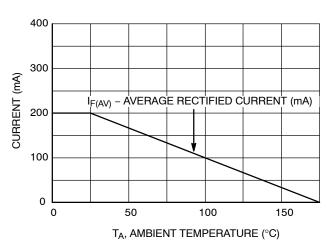


Figure 8. Average Rectified Current (I_{F(AV)}) vs. Ambient Temperature (T_A)

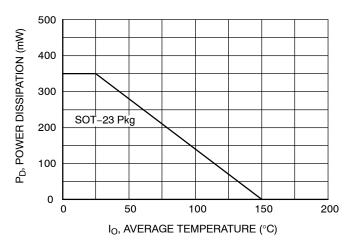


Figure 9. Power Derating Curve

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ORDERING INFORMATION

Part Number	Top Mark	Package	Pinout	Pinout Style	Shipping [†]
MMBD4148SE	D4	SOT-23 (Pb-Free)	pin 1 = Anode, pin 2 = Cathode, pin 3 = Cathode/Anode	Style 11	3,000 / Tape & Reel
MMBD4148CC	D5		pin 1 = Anode, pin 2 = Anode, pin 3 = Cathode	Style 23	3,000 / Tape & Reel
MMBD4148CA	D6		pin 1 = Cathode, pin 2 = Cathode, pin 3 = Anode/Anode	Style 12	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

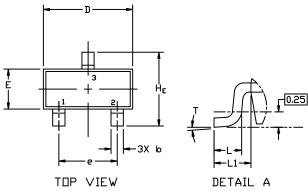




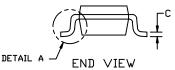
SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10*



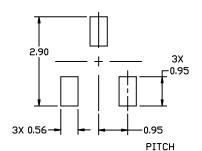


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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